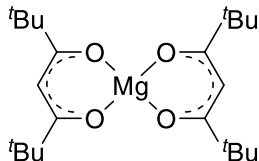


Catalog # 12-0900 Bis(2,2,6,6-tetramethyl-3,5-heptanedionato)magnesium, anhydrous, min. 98%
[Mg(TMHD)2]



Thermal Behavior:

- Melting point 94-95°C [1], 122-126°C [2]
- Sublimation 120°C/0.15 Torr [2]
- TGA Data and diagram is available in [2, 5]

Technical Notes:

1. Precursor for magnesium thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
MgO	ALD	110°C	7.5 Torr	H ₂ O ₂	325-425°C	2
	ALD	170°C	0.75 Torr	O ₃	180-450°C	3
	CVD	200°C	37.5 Torr-AP	O ₂	400-500°C	4
	CVD	240-300°C	AP	Air	400-600°C	5
MgF	ALD	125°C	7.5 Torr	TiF ₄	250-400°C	6
	ALD	125°C	7.5 Torr	TiF ₅	225-400°C	7
	ALD	-	-	Hhfac, O ₃	300°C	8
FeMg _x O _y	ALD	170°C	-	CpFeC ₅ H ₄ CHNMe ₂ , O ₃	350-500°C	9
Pb(Mg _{1/3} Nb _{2/3})O ₃	CVD	120-135°C	6 Torr	PbEt ₄ , Nb(OEt) ₅ , O ₂	700-780°C	10
Cu(Cr _{1-x} Mg _x)O ₂	ALD	150°C	1.5-2.25 Torr	Cu(thd) ₂ , Cr(acac) ₃ , O ₃	250°C	11

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